

# Bui Nguyen Quoc Trinh

## List of Publications by Year in descending order

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33  
papers

188  
citations

1307594

7  
h-index

1125743

13  
g-index

34  
all docs

34  
docs citations

34  
times ranked

173  
citing authors

#	ARTICLE	IF	CITATIONS
1	Totally solution-processed ferroelectric-gate thin-film transistor. Applied Physics Letters, 2010, 97, .	3.3	36
2	A low-temperature crystallization path for device-quality ferroelectric films. Applied Physics Letters, 2010, 97, .	3.3	33
3	Ferroelectric-Gate Thin-Film Transistor Fabricated by Total Solution Deposition Process. Japanese Journal of Applied Physics, 2011, 50, 04DD09.	1.5	19
4	Low-temperature PZT thin-film ferroelectric memories fabricated on SiO <sub>2</sub> /Si and glass substrates. Journal of Science: Advanced Materials and Devices, 2016, 1, 75-79.	3.1	16
5	Optimization of Pt and PZT Films for Ferroelectric-Gate Thin Film Transistors. Ferroelectrics, 2010, 405, 281-291.	0.6	12
6	Synthesis of undoped and M-doped ZnO (M = Co, Mn) nanopowder in water using microwave irradiation. Journal of Physics: Conference Series, 2009, 187, 012020.	0.4	10
7	Interface Charge Trap Density of Solution Processed Ferroelectric Gate Thin Film Transistor Using ITO/PZT/Pt Structure. Ferroelectrics, Letters Section, 2013, 40, 17-29.	1.0	7
8	Solution-Processed Cupric Oxide P-type Channel Thin-Film Transistors. Thin Solid Films, 2020, 704, 137991.	1.8	7
9	Solution-processed CuO thin films with various Cu <sup>2+</sup> ion concentrations. Thin Solid Films, 2018, 660, 819-823.	1.8	6
10	Fabrication and characterization of a ferroelectric-gate FET With a ITO/PZT/SRO/Pt stacked structure. , 2010, , .		5
11	Solution processed In-Si-O thin film transistors on hydrophilic and hydrophobic substrates. Thin Solid Films, 2020, 698, 137860.	1.8	5
12	Nondestructive Readout of Ferroelectric-Gate Field-Effect Transistor Memory With an Intermediate Electrode by Using an Improved Operation Method. IEEE Transactions on Electron Devices, 2008, 55, 3200-3207.	3.0	4
13	Fabrication of 120-nm-channel-length ferroelectric-gate thin-film transistor by nanoimprint lithography. Japanese Journal of Applied Physics, 2014, 53, 02BC14.	1.5	4
14	Operation of Ferroelectric Gate Field-Effect Transistor Memory with Intermediate Electrode using Polycrystalline Capacitor and Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor. Japanese Journal of Applied Physics, 2006, 45, 7341-7344.	1.5	3
15	Control of Preferential Orientation of Platinum Films on RuO <sub>2</sub> /SiO <sub>2</sub> /Si Substrates by Sputtering. Japanese Journal of Applied Physics, 2006, 45, 8810-8816.	1.5	3
16	Switchable voltage control of the magnetic anisotropy in heterostructured nanocomposites of CoFe/NiFe/PZT. Journal of the Korean Physical Society, 2013, 63, 812-816.	0.7	2
17	Silicon-doped indium oxide â€“ a promising amorphous oxide semiconductor material for thin-film transistor fabricated by spin coating method. IOP Conference Series: Materials Science and Engineering, 2019, 625, 012002.	0.6	2
18	Solution-processable zinc oxide based thin films with different aluminum doping concentrations. Journal of Science: Advanced Materials and Devices, 2020, 5, 497-501.	3.1	2

#	ARTICLE	IF	CITATIONS
19	Spin reorientation in ErCo <sub>10</sub> xFeMo <sub>2</sub> compounds. Physica B: Condensed Matter, 2003, 327, 262-265.	2.7	1
20	Fabrication of Polycrystalline Ferroelectric Gate FET Memory with an Intermediate Electrode. Applications of Ferroelectrics, IEEE International Symposium on, 2006, , .	0.0	1
21	Improvement of Nondestructive Readout of Ferroelectric Gate FET Memory with an Intermediate Electrode by using New Data Writing and Reading Methods. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	1
22	Disturb-Free Writing Operation for Ferroelectric-Gate Field-Effect Transistor Memories With Intermediate Electrodes. IEEE Transactions on Electron Devices, 2009, 56, 3090-3096.	3.0	1
23	Analysis on interface layer between Pt electrode and ferroelectric layer of solution-processed PZT capacitor. Materials Research Society Symposia Proceedings, 2011, 1368, 1.	0.1	1
24	Electric Properties and Interface Charge Trap Density of Ferroelectric Gate Thin Film Transistor Using (Bi,La) <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> /Pb(Zr,Ti)O <sub>3</sub> Stacked Gate Insulator. Japanese Journal of Applied Physics, 2012, 51, 09LA09.	1.5	1
25	Investigation on solution-processed In-Si-O thin-film transistor via spin-coating method. , 2018, , .		1
26	Electric Properties and Interface Charge Trap Density of Ferroelectric Gate Thin Film Transistor Using (Bi,La) <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> /Pb(Zr,Ti)O <sub>3</sub> Stacked Gate Insulator. Japanese Journal of Applied Physics, 2012, 51, 09LA09.	1.5	1
27	Conductive-perovskite LaNiO <sub>3</sub> thin films prepared by using solution process for electrode application. VNU Journal of Science Mathematics - Physics, 2018, 34, .	0.1	1
28	Lanthanum Oxide Capping Layer for Solution-Processed Ferroelectric-Gate Thin-Film Transistors. Materials Research Society Symposia Proceedings, 2011, 1337, 117.	0.1	0
29	Sub-100Ånm Ferroelectric-Gate Thin-Film Transistor with Low-Temperature PZT Fabricated on SiO <sub>2</sub> /Si Substrate. Ferroelectrics, Letters Section, 2015, 42, 65-74.	1.0	0
30	Epitaxial-like growth of solution-processed PbZr <sub>0.4</sub> Ti <sub>0.6</sub> O <sub>3</sub> thin film on single-crystal Nb-doped SrTiO <sub>3</sub> substrate. VNU Journal of Science Mathematics - Physics, 2018, 33, .	0.1	0
31	INVESTIGATION ON STRUCTURAL AND FERROELECTRIC PROPERTIES OF Bi <sub>3.25</sub> La <sub>0.75</sub> Ti <sub>3</sub> O <sub>12</sub> THIN FILMS. Science and Technology, 2018, 54, 80.	0.2	0
32	STUDY ON ITO THIN FILMS PREPARED BY MULTI-ANNEALING TECHNIQUE. Science and Technology, 2018, 54, 136.	0.2	0
33	Demonstration on Ferroelectric-gate Thin Film Transistor NAND-type Array with Disturbance-free Operation. VNU Journal of Science Mathematics - Physics, 2019, 35, .	0.1	0